

## -20V P-Channel Trench Power MOSFET

### Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	$I_D$
-20V	350mΩ@-4.5V	-0.66A
	450mΩ@-2.5V	

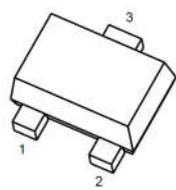
### Features

- Very Low On-resistance  $R_{DS(ON)}$
- Low  $C_{rSS}$
- Fast switching
- ESD Protected Up to 2.0KV (HBM)

### Applications

- Interfacing, Logic switch
- Load switch
- Power management

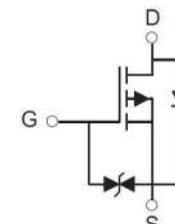
**SOT-723**



PIN1:GATE  
PIN2:SOURCE  
PIN3:DRAIN

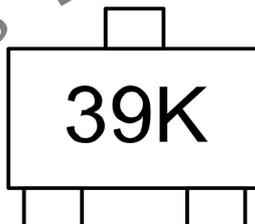
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**Schematic diagram**




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**Marking**



### Absolute Maximum rating ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

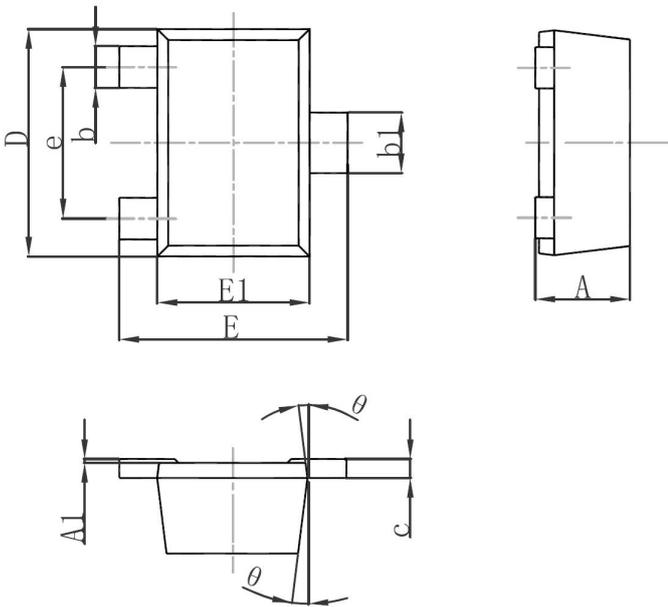
Parameter	Symbol	Value	Units	
Drain-Source Voltage	$V_{DS}$	-20	V	
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V	
Drain Current	$I_D$	$T_C = 25^\circ\text{C}$	-0.66	A
		$T_C = 100^\circ\text{C}$	-0.4	A
Drain Current - Pulsed	$I_{DM}$	-2	A	
Power Dissipation	$P_D$	0.15	W	
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	833	$^\circ\text{C}/\text{W}$	
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$	

**Electrical Characteristics (T<sub>A</sub> = 25°C unless otherwise noted)**

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
<b>Static Characteristics</b>						
Drain - Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA	-20			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V			1	μA
Gate - Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±10V, V <sub>DS</sub> = 0V			±10	μA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA	-0.35	-0.65	-1	V
Drain-source On-resistance	R <sub>DSON</sub>	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -0.5A		350	450	mΩ
		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -0.4A		450	600	
<b>Dynamic Characteristics</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0V, f = 1MHz		65		pF
Output Capacitance	C <sub>oss</sub>			15		
Reverse Transfer Capacitance	C <sub>rss</sub>			8		
<b>Switching Characteristics</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> = -4.5V, V <sub>DD</sub> = -10V, I <sub>D</sub> = -0.5A		1.15		nC
Gate-source Charge	Q <sub>gs</sub>			0.37		
Gate-drain Charge	Q <sub>gd</sub>			0.25		
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>GS</sub> = -4.5V, V <sub>DD</sub> = -10V, I <sub>D</sub> = -0.5A, R <sub>GEN</sub> = 3Ω		4		ns
Turn-on Rise Time	t <sub>r</sub>			19		
Turn-off Delay Time	t <sub>d(off)</sub>			16		
Turn-off Fall Time	t <sub>f</sub>			25		
<b>Source - Drain Diode Characteristics</b>						
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0V, I <sub>S</sub> = -0.5A			-1.2	V
Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>S</sub> = -0.5A, dI <sub>F</sub> / dt = 100 A/us		0.97		ns
Peak Reverse Recovery Current	I <sub>rr</sub>				26	

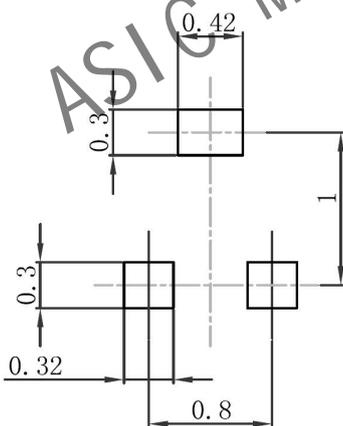
## Dimension

### SOT-723



Symbol	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	0.400	0.500	0.015	0.020
A1	0.000	0.050	0.000	0.002
b	0.170	0.270	0.007	0.011
b1	0.270	0.370	0.011	0.015
c	0.080	0.150	0.003	0.006
D	1.150	1.250	0.045	0.049
E	1.150	1.250	0.045	0.049
E1	0.750	0.850	0.030	0.033
e	0.800TYP.		0.031TYP.	
θ	7° REF.		7° REF.	

## Recommended Land Pattern



### Note:

1. Controlling dimension: in millimeters
2. General tolerance:  $\pm 0.05\text{mm}$
3. The pad layout is for reference only
4. Unit: mm